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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet	1	Of	8

COMPLETE IF KNOWN	
Application Number	10/078,474
Filing Date	2-21-02
First Named Inventor	Ho Ki Kwon
Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002769

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U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No[1]	Document Number: Number	Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
DN		US 4445218		04-24-1984	Coldren	
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Examiner Signature		Date Considered	05/17/04

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Sheet	2	Of	8

COMPLETE IF KNOWN	
Application Numb r	10/078,474
Filing Date	2-21-02
First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002769

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Sheet	3	Of	8

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First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002769

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First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002769

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No[1]	Foreign Patent Document: Country Code[3]	Number[4]	Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T[6]
DV	✓	EP	0 740 377	A1	10-30-1996	Hewlett-Packard Company		
	✓	EP	0 740 377	B	10-30-1996	Hewlett-Packard Company		
	✓	EP	0 765 014	A1	03-26-1997	France Telecom		
	✓	EP	0 765 014	B1	07-28-1999	France Telecom		
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	✓	EP	0 874 428	A2	10-28-1998	Motorola, Inc.		
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	✓	WO	00/052789	A3	02-29-2000	The Regents of the University of California		
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	✓	WO	01/017076	A2	03-08-2001	The Regents of the University of California		

Examiner Signature	DV	Date Considered	05/17/04

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Applicati n Number	10/078,474
Filing Date	2-21-02
First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002769

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		✓	WO	01/018919	A1	03-15-2001	The Regents of the University of California	
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T[2]
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COMPLETE IF KNOWN	
Applicati n Numb r	10/078,474
Filing Date	2-21-02
First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002769

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Examiner Signature		Date Considered	05/17/04

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Attorney Docket Number	H0002769

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Examiner Signature		Date Considered	05/17/05

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Application Number	10/078,474
Filing Date	2-21-02
First Named Inventor	Ho Ki Kwon
Group Art Unit	2828
Examiner Name	Dung T. Nguyen
Attorney Docket Number	H0002769

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